

Magnetoplasma resonance in electron-hole drops germanium at submillimeter wavelengths

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We investigated the magnetoplasma resonance spectra in electron-hole drops (EHD) in germanium in the submillimeter wavelength band 440–770 μ in magnetic fields up to 35 kOe. The renormalized carrier masses in the EHD were determined experimentally.

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In the first investigations of magnetoplasma resonance (MPR) in electron-hole drops (EHD) in germanium, performed in the far IR region,^[1] splitting of the resonance absorption band of the EHD in a magnetic field was observed together with the appearance of singularities on the long-wave absorption edge. These changes were explained on the basis of the developed model of MPR in EHD,^[1–3] according to which, when a magnetic field is applied, a splitting of the plasma resonance of the EHD should occur, together with hybrid magnetoplasma oscillations in the region of the cyclotron frequencies of the free carriers. In the investigations of^[1,2], owing to the insufficient spectral resolution, it was impossible to study the long-wave part of the MPR in EHD. This region of the MPR in EHD in Ge was investigated later at several discrete points of the spectrum.^[4–6]

In this study, using the methods of monochromatic submillimeter spectroscopy based on backward wave tubes (BWT),^[7,8] we investigated for the first time the long-wave part of MPR in EHD in germanium with smooth scanning over the spectrum in the region 1.6–2.8 meV ($\lambda = 440 - 770 \mu$), that is, both the exciton-absorption region^[8] and beyond its limits. We studied the change in the parameters of the MPR lines as functions of the photon energy and showed experimentally that the effective mass of the carriers in the EHD differs from the mass of the free carriers in Ge.

Measurements of the change in the transmission of samples of pure Ge ($N_A \approx 10^{12} \text{ cm}^{-3}$) at submillimeter wavelengths following optical generation of non-equilibrium carriers was carried out by the BWT method^[8] at temperature 4.2–1.9°K in a light-pipe cryostat used earlier to study a MPR in EHD

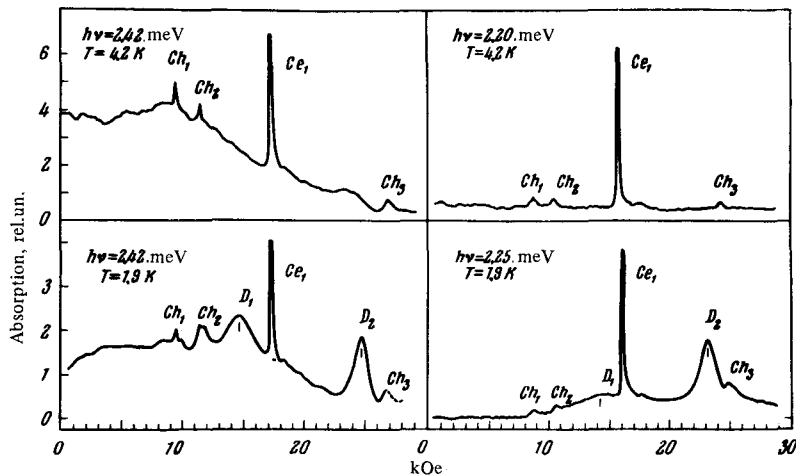


Fig. 1. MPR spectra in EHD in germanium.

Ge in the region of the EHD plasma resonance.^[1] The investigations were carried out at the orientation $\mathbf{H} \parallel [111]$ in fields up to 35 kOe at the Faraday configuration $E_{\omega} \perp \mathbf{H}$.

Figure 1 shows typical spectra measured at 4.2 and 1.9°K in the region of exciton absorption ($\hbar\omega = 2.42$ meV)^[8] and beyond its limits ($\hbar\omega = 2.25$ meV). The spectra show the nonequilibrium-electron CR lines Ce_1 , the energy ellipsoid of which is elongated along \mathbf{H} , and the lines Ch_1 , Ch_2 , and Ch_3 corresponding to transitions between the Landau levels of the valence band deformed in magnetic field.^[5,9] The absorption at 2.42 meV in weak magnetic fields is due to photoexcitation of free excitons^[7,8] and decreases with increasing field, since the exciton spectrum shifts towards higher energies.

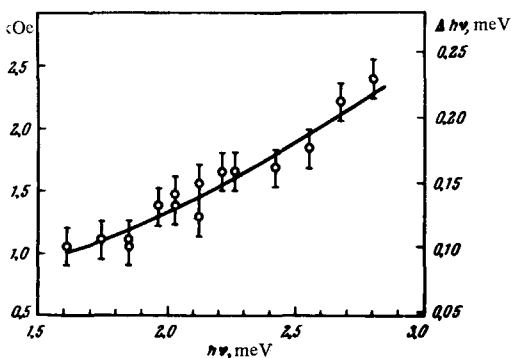


Fig. 2. Dependence of the half-width of the D_2 line on the photon energy.

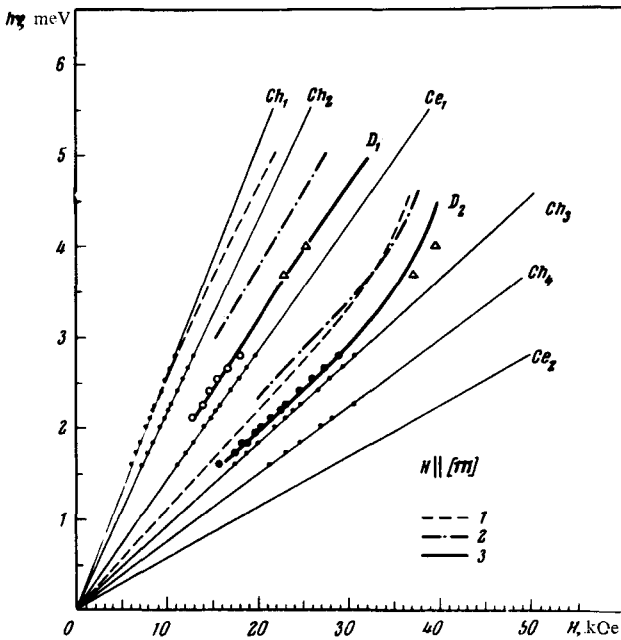


Fig. 3. Spectral positions of the CR lines of the free carriers and of the lines of the MPR in EHD in germanium (points and circles—our experimental data, triangles—data of ^[5]); calculated curves: 1—from the model of ^[3], 2—with allowance for the quantum deformations of the valence band of Ge, 3—the same for the altered carrier masses.

When the temperature is lowered to 1.9 °K, a decrease of the intensity of the exciton absorption is observed, due to the exciton transition to the condensed state and to the appearance in the spectrum of new quite broad lines D_1 and D_2 . The appearance of these lines, as well as their spectral position relative to the CR lines of the free carriers, agree with the predictions of the model of the MPR in EHD in germanium, developed in ^[1-3]. The intensity of the lines D_1 and D_2 decreases with increasing wavelength (the expression for the MPR intensity contains the factor ^[3] λ^{-1}) the line D_1 being broader and attenuating more rapidly with the wavelength than the line D_2 (it is hardly seen in Fig. 2, at 2.25 meV). The half-width of the line D_2 , as seen from Fig. 2, is approximately 0.2 meV (damping constant $\gamma \approx 2.5 \cdot 10^{11} \text{ sec}^{-1}$), it differs by more than one order of magnitude from the half-width of the plasma resonance measured in the 9-meV region ^[1], and decreases with increasing wavelength. The possibility of such a frequency dependence of γ was noted in ^[1] in connection with a discussion of various mechanisms of the damping of plasma oscillations in EHD in germanium.

Figure 3 shows the results of measurements of the spectral dependence of the MPR in EHD and of the quantum cyclotron resonance in a system of free carriers, and also the results of theoretical calculations of the MPR in EHD on the basis of the model of ^[3]. According to this model, a resonant MPR fre-

ency appears between any two CR frequencies of equal sign and circular polarization. Consequently the line D_1 is due to the presence of light and heavy holes, while the line D_2 is due to the presence, in the given orientation, of two groups of electrons with different cyclotron frequencies (Ce_1 and Ce_2). The positions of these lines in fields up to 20–30 kOe, as noted in [2,3] and as shown by numerical calculations, differs little on the carrier density in the EHD, and is determined mainly by the carrier masses. This makes it possible in principle to estimate from our measurement data the values of the effective masses of the carriers in the EHD. As seen from Fig. 3, the calculation performed on the basis of the free-carrier parameters in Ge, even with allowance for the quantum deformations of the valence band of Ge in the magnetic field, [9] still does not make it possible to describe satisfactorily experimental results. This indicates that the effective carrier mass in the EHD differs from the mass of the free carriers in Ge. Good agreement with experiment was obtained for electron masses $m_{\text{I}}^{\text{EHD}} = 1.1 m_{\text{I}}$ and $m_{\text{II}}^{\text{EHD}} = m_{\text{II}}$ and for valence-band hole masses $m_{\text{I}}^{\text{EHD}} = 0.85 m_{\text{I}}$ and $m_{\text{II}}^{\text{EHD}} = 0.85 m_{\text{II}}$ (the carrier masses in EHD as a result of multiparticle effects). [10] We note that the theoretical dependence of the position of D_2 , calculated for a carrier concentration $n_k = 2 \cdot 10^{17} \text{ cm}^{-3}$ in the EHD, differs from the experimental value in fields $H \geq 35 \text{ Oe}$. This difference, due to the incipient emergence of the zero Landau level of the "light" electrons beyond the limits of the Fermi level, shows that the concentration n_k in the EHD greatly increases in these fields.

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